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What is "[Embedded - Microcontrollers](#)"?

"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Obsolete
Core Processor	RL78
Core Size	16-Bit
Speed	32MHz
Connectivity	CSI, I ² C, LINbus, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	31
Program Memory Size	32KB (32K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	2K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 10x8/10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	44-LQFP
Supplier Device Package	44-LQFP (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f101fcdfp-x0

Table 1-1. List of Ordering Part Numbers

(2/12)

Pin count	Package	Data flash	Fields of Application Note	Ordering Part Number
25 pins	25-pin plastic WFLGA (3 × 3 mm, 0.5 mm pitch)	Mounted	A G	R5F1008AALA#U0, R5F1008CALA#U0, R5F1008DALA#U0, R5F1008EALA#U0 R5F1008AALA#W0, R5F1008CALA#W0, R5F1008DALA#W0, R5F1008EALA#W0 R5F1008AGLA#U0, R5F1008CGLA#U0, R5F1008DGLA#U0, R5F1008EGLA#U0 R5F1008AGLA#W0, R5F1008CGLA#W0, R5F1008DGLA#W0, R5F1008EGLA#W0
		Not mounted	A	R5F1018AALA#U0, R5F1018CALA#U0, R5F1018DALA#U0, R5F1018EALA#U0 R5F1018AALA#W0, R5F1018CALA#W0, R5F1018DALA#W0, R5F1018EALA#W0
30 pins	30-pin plastic LSSOP (7.62 mm (300), 0.65 mm pitch)	Mounted	A D G	R5F100AAASP#V0, R5F100ACASP#V0, R5F100ADASP#V0, R5F100AEASP#V0, R5F100AFASP#V0, R5F100AGASP#V0 R5F100AAASP#X0, R5F100ACASP#X0, R5F100ADASP#X0, R5F100AEASP#X0, R5F100AFASP#X0, R5F100AGASP#X0 R5F100AADSP#V0, R5F100ACDSP#V0, R5F100ADDSP#V0, R5F100AEDSP#V0, R5F100AFDSP#V0, R5F100AGDSP#V0 R5F100AADSP#X0, R5F100ACDSP#X0, R5F100ADDSP#X0, R5F100AEDSP#X0, R5F100AFDSP#X0, R5F100AGDSP#X0 R5F100AAGSP#V0, R5F100ACGSP#V0, R5F100ADGSP#V0, R5F100AEGSP#V0, R5F100AFGSP#V0, R5F100AGGSP#V0 R5F100AAGSP#X0, R5F100ACGSP#X0, R5F100ADGSP#X0, R5F100AEGSP#X0, R5F100AFGSP#X0, R5F100AGGSP#X0
		Not mounted	A D	R5F101AAASP#V0, R5F101ACASP#V0, R5F101ADASP#V0, R5F101AEASP#V0, R5F101AFASP#V0, R5F101AGASP#V0 R5F101AAASP#X0, R5F101ACASP#X0, R5F101ADASP#X0, R5F101AEASP#X0, R5F101AFASP#X0, R5F101AGASP#X0 R5F101AADSP#V0, R5F101ACDSP#V0, R5F101ADDSP#V0, R5F101AEDSP#V0, R5F101AFDSP#V0, R5F101AGDSP#V0 R5F101AADSP#X0, R5F101ACDSP#X0, R5F101ADDSP#X0, R5F101AEDSP#X0, R5F101AFDSP#X0, R5F101AGDSP#X0
32 pins	32-pin plastic HWQFN (5 × 5 mm, 0.5 mm pitch)	Mounted	A D G	R5F100BAANA#U0, R5F100BCANA#U0, R5F100BDANA#U0, R5F100BEANA#U0, R5F100BFANA#U0, R5F100BGANA#U0 R5F100BAANA#W0, R5F100BCANA#W0, R5F100BDANA#W0, R5F100BEANA#W0, R5F100BFANA#W0, R5F100BGANA#W0 R5F100BADNA#U0, R5F100BCDNA#U0, R5F100BDDNA#U0, R5F100BEDNA#U0, R5F100BFDNA#U0, R5F100BGDNA#U0 R5F100BADNA#W0, R5F100BCDNA#W0, R5F100BDDNA#W0, R5F100BEDNA#W0, R5F100BFDNA#W0, R5F100BGDNA#W0 R5F100BAGNA#U0, R5F100BCGNA#U0, R5F100BDGNA#U0, R5F100BEGNA#U0, R5F100BFGNA#U0, R5F100BGGNA#U0 R5F100BAGNA#W0, R5F100BCGNA#W0, R5F100BDGNA#W0, R5F100BEGNA#W0, R5F100BFGNA#W0, R5F100BGGNA#W0
		Not mounted	A D	R5F101BAANA#U0, R5F101BCANA#U0, R5F101BDANA#U0, R5F101BEANA#U0, R5F101BFANA#U0, R5F101BGANA#U0 R5F101BAANA#W0, R5F101BCANA#W0, R5F101BDANA#W0, R5F101BEANA#W0, R5F101BFANA#W0, R5F101BGANA#W0 R5F101BADNA#U0, R5F101BCDNA#U0, R5F101BDDNA#U0, R5F101BEDNA#U0, R5F101BFDNA#U0, R5F101BGDNA#U0 R5F101BADNA#W0, R5F101BCDNA#W0, R5F101BDDNA#W0, R5F101BEDNA#W0, R5F101BFDNA#W0, R5F101BGDNA#W0

Note For the fields of application, refer to **Figure 1-1 Part Number, Memory Size, and Package of RL78/G13**.

Caution The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.

Table 1-1. List of Ordering Part Numbers

(12/12)

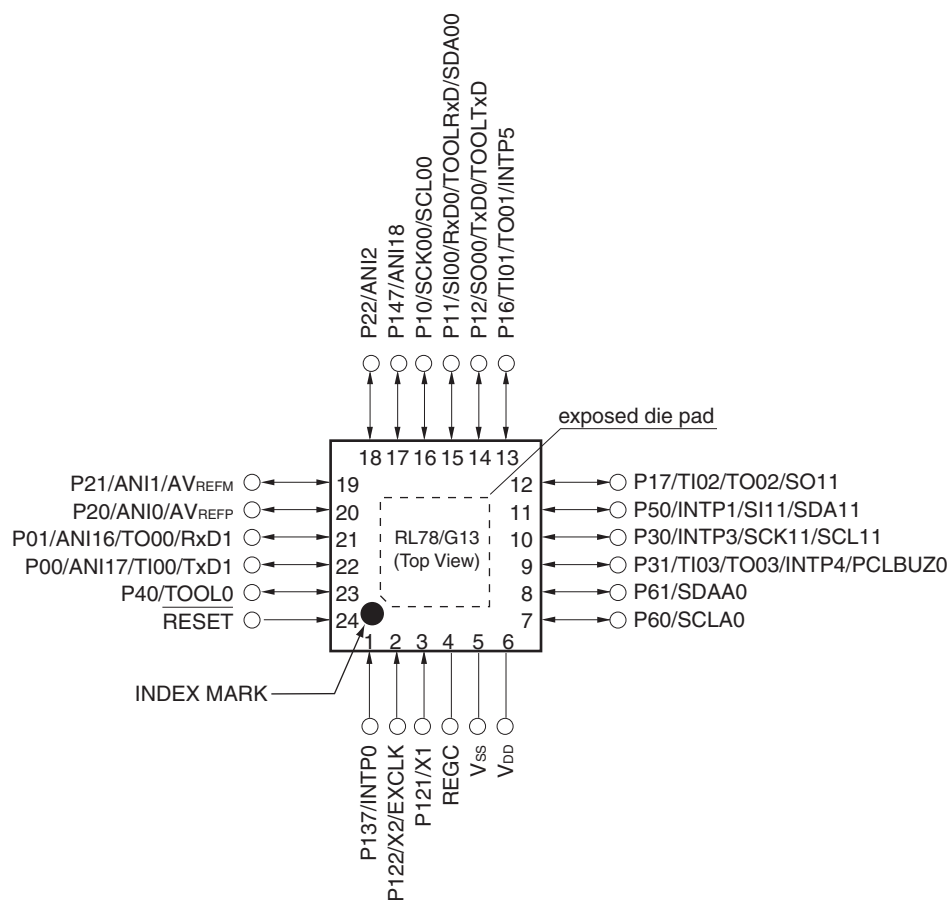
Pin count	Package	Data flash	Fields of Application ^{Note}	Ordering Part Number
128 pins	128-pin plastic LFQFP (14 × 20 mm, 0.5 mm pitch)	Mounted	A	R5F100SHAFB#V0, R5F100SJAFB#V0, R5F100SKAFB#V0, R5F100SLAFB#V0 R5F100SHAFB#X0, R5F100SJAFB#X0, R5F100SKAFB#X0, R5F100SLAFB#X0
			D	R5F100SHDFB#V0, R5F100SJDFB#V0, R5F100SKDFB#V0, R5F100SLDFB#V0 R5F100SHDFB#X0, R5F100SJDFB#X0, R5F100SKDFB#X0, R5F100SLDFB#X0
		Not mounted	A	R5F101SHAFB#V0, R5F101SJAFB#V0, R5F101SKAFB#V0, R5F101SLAFB#V0 R5F101SHAFB#X0, R5F101SJAFB#X0, R5F101SKAFB#X0, R5F101SLAFB#X0
			D	R5F101SHDFB#V0, R5F101SJDFB#V0, R5F101SKDFB#V0, R5F101SLDFB#V0 R5F101SHDFB#X0, R5F101SJDFB#X0, R5F101SKDFB#X0, R5F101SLDFB#X0

Note For the fields of application, refer to **Figure 1-1 Part Number, Memory Size, and Package of RL78/G13**.

Caution The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.

1.3.2 24-pin products

- 24-pin plastic HWQFN (4 × 4 mm, 0.5 mm pitch)



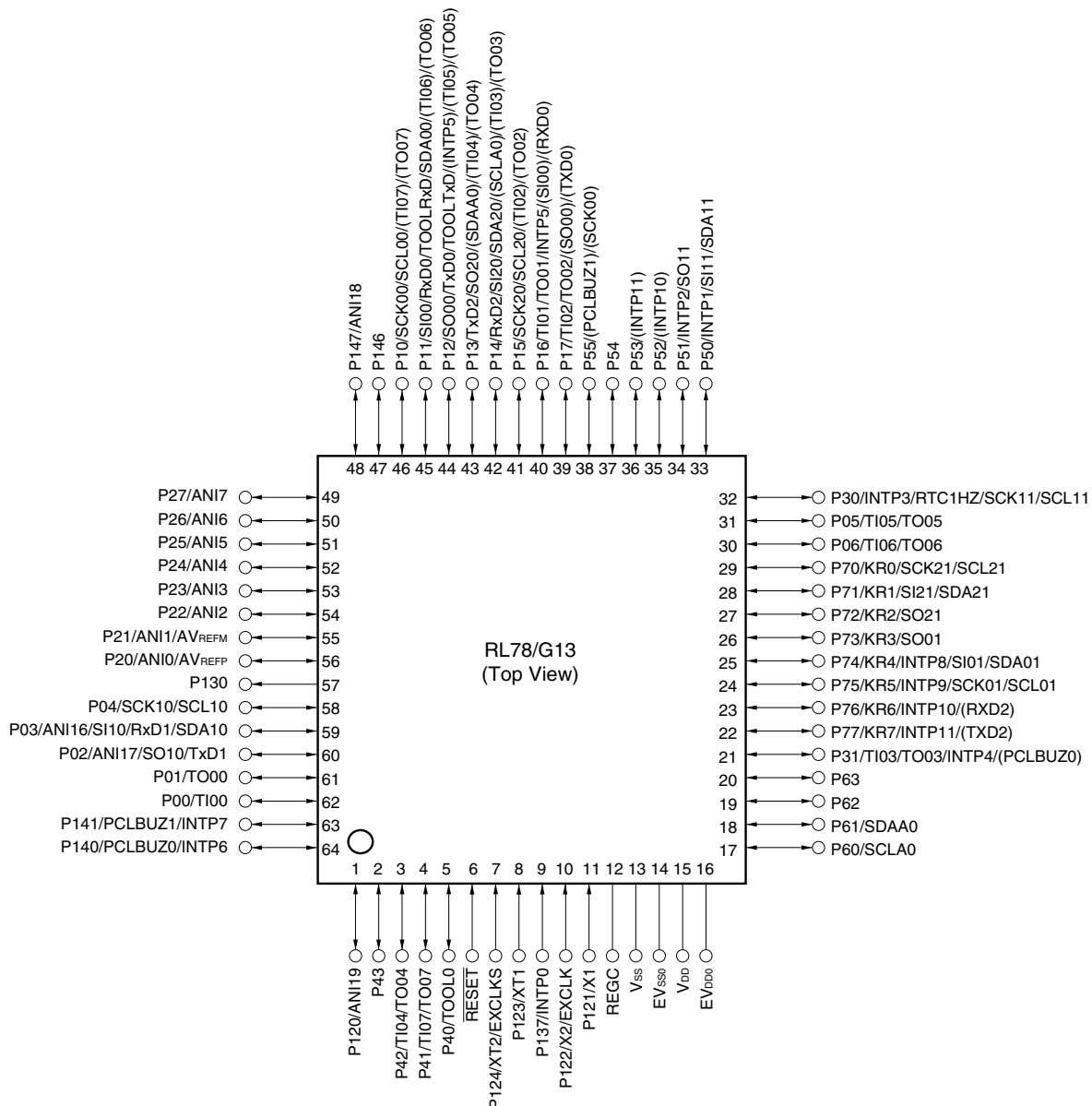
Caution Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F).

Remarks 1. For pin identification, see 1.4 Pin Identification.

2. It is recommended to connect an exposed die pad to Vss.

1.3.11 64-pin products

- 64-pin plastic LQFP (12 × 12 mm, 0.65 mm pitch)
- 64-pin plastic LFQFP (10 × 10 mm, 0.5 mm pitch)



- Cautions**
1. Make EV_{SS0} pin the same potential as V_{SS} pin.
 2. Make V_{DD} pin the potential that is higher than EV_{DD0} pin.
 3. Connect the REGC pin to V_{SS} via a capacitor (0.47 to 1 μ F).

- Remarks**
1. For pin identification, see 1.4 Pin Identification.
 2. When using the microcontroller for an application where the noise generated inside the microcontroller must be reduced, it is recommended to supply separate powers to the V_{DD} and EV_{DD0} pins and connect the V_{SS} and EV_{SS0} pins to separate ground lines.
 3. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to **Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR)** in the RL78/G13 User's Manual.

2. ELECTRICAL SPECIFICATIONS ($T_A = -40$ to $+85^\circ\text{C}$)

This chapter describes the following electrical specifications.

Target products A: Consumer applications $T_A = -40$ to $+85^\circ\text{C}$

R5F100xxAxx, R5F101xxAxx

D: Industrial applications $T_A = -40$ to $+85^\circ\text{C}$

R5F100xxDxx, R5F101xxDxx

G: Industrial applications when $T_A = -40$ to $+105^\circ\text{C}$ products is used in the range of $T_A = -40$ to $+85^\circ\text{C}$

R5F100xxGxx

- Cautions**
1. The RL78 microcontrollers have an on-chip debug function, which is provided for development and evaluation. Do not use the on-chip debug function in products designated for mass production, because the guaranteed number of rewritable times of the flash memory may be exceeded when this function is used, and product reliability therefore cannot be guaranteed. Renesas Electronics is not liable for problems occurring when the on-chip debug function is used.
 2. With products not provided with an EV_{DD0} , EV_{DD1} , EV_{SS0} , or EV_{SS1} pin, replace EV_{DD0} and EV_{DD1} with V_{DD} , or replace EV_{SS0} and EV_{SS1} with V_{SS} .
 3. The pins mounted depend on the product. Refer to 2.1 Port Function to 2.2.1 Functions for each product.

(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) (1/2)**(T_A = -40 to +85°C, 1.8 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V)**

Parameter	Symbol	Conditions		HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit	
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.		
Transfer rate		Reception	4.0 V ≤ EV _{DD0} ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V			f _{MCK} /6 Note 1		f _{MCK} /6 Note 1		f _{MCK} /6 Note 1	bps
						5.3		1.3		0.6	Mbps
			Theoretical value of the maximum transfer rate f _{MCK} = f _{CLK} ^{Note 4}								
						5.3		1.3		0.6	Mbps
			2.7 V ≤ EV _{DD0} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V			f _{MCK} /6 Note 1		f _{MCK} /6 Note 1		f _{MCK} /6 Note 1	bps
						5.3		1.3		0.6	Mbps
1.8 V ≤ EV _{DD0} < 3.3 V, 1.6 V ≤ V _b ≤ 2.0 V			f _{MCK} /6 Notes 1 to 3		f _{MCK} /6 Notes 1, 2		f _{MCK} /6 Notes 1, 2	bps			
			5.3		1.3		0.6	Mbps			
Theoretical value of the maximum transfer rate f _{MCK} = f _{CLK} ^{Note 4}											

Notes 1. Transfer rate in the SNOOZE mode is 4800 bps only.**2.** Use it with EV_{DD0} ≥ V_b.**3.** The following conditions are required for low voltage interface when EV_{DD0} < V_{DD}.2.4 V ≤ EV_{DD0} < 2.7 V : MAX. 2.6 Mbps1.8 V ≤ EV_{DD0} < 2.4 V : MAX. 1.3 Mbps**4.** The maximum operating frequencies of the CPU/peripheral hardware clock (f_{CLK}) are:HS (high-speed main) mode: 32 MHz (2.7 V ≤ V_{DD} ≤ 5.5 V)16 MHz (2.4 V ≤ V_{DD} ≤ 5.5 V)LS (low-speed main) mode: 8 MHz (1.8 V ≤ V_{DD} ≤ 5.5 V)LV (low-voltage main) mode: 4 MHz (1.6 V ≤ V_{DD} ≤ 5.5 V)

Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (V_{DD} tolerance (When 20- to 52-pin products)/EV_{DD} tolerance (When 64- to 128-pin products)) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

Remarks 1. V_b[V]: Communication line voltage**2.** q: UART number (q = 0 to 3), g: PIM and POM number (g = 0, 1, 8, 14)**3.** f_{MCK}: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13))

4. UART2 cannot communicate at different potential when bit 1 (PIOR1) of peripheral I/O redirection register (PIOR) is 1.

(9) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (slave mode, SCKp... external clock input)

(T_A = -40 to +85°C, 1.8 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V) (1/2)

Parameter	Symbol	Conditions		HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time ^{Note 1}	t _{KCY2}	4.0 V ≤ EV _{DD0} ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V	24 MHz < f _{MCK}	14/ f _{MCK}		—		—		ns
			20 MHz < f _{MCK} ≤ 24 MHz	12/ f _{MCK}		—		—		ns
			8 MHz < f _{MCK} ≤ 20 MHz	10/ f _{MCK}		—		—		ns
			4 MHz < f _{MCK} ≤ 8 MHz	8/f _{MCK}		16/ f _{MCK}		—		ns
			f _{MCK} ≤ 4 MHz	6/f _{MCK}		10/ f _{MCK}		10/ f _{MCK}		ns
		2.7 V ≤ EV _{DD0} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V	24 MHz < f _{MCK}	20/ f _{MCK}		—		—		ns
			20 MHz < f _{MCK} ≤ 24 MHz	16/ f _{MCK}		—		—		ns
			16 MHz < f _{MCK} ≤ 20 MHz	14/ f _{MCK}		—		—		ns
			8 MHz < f _{MCK} ≤ 16 MHz	12/ f _{MCK}		—		—		ns
			4 MHz < f _{MCK} ≤ 8 MHz	8/f _{MCK}		16/ f _{MCK}		—		ns
			f _{MCK} ≤ 4 MHz	6/f _{MCK}		10/ f _{MCK}		10/ f _{MCK}		ns
		1.8 V ≤ EV _{DD0} < 3.3 V, 1.6 V ≤ V _b ≤ 2.0 V ^{Note 2}	24 MHz < f _{MCK}	48/ f _{MCK}		—		—		ns
			20 MHz < f _{MCK} ≤ 24 MHz	36/ f _{MCK}		—		—		ns
			16 MHz < f _{MCK} ≤ 20 MHz	32/ f _{MCK}		—		—		ns
			8 MHz < f _{MCK} ≤ 16 MHz	26/ f _{MCK}		—		—		ns
			4 MHz < f _{MCK} ≤ 8 MHz	16/ f _{MCK}		16/ f _{MCK}		—		ns
			f _{MCK} ≤ 4 MHz	10/ f _{MCK}		10/ f _{MCK}		10/ f _{MCK}		ns

(Notes and Caution are listed on the next page, and Remarks are listed on the page after the next page.)

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- Notes**
1. The first clock pulse is generated after this period when the start/restart condition is detected.
 2. The maximum value (MAX.) of t_{HD:DAT} is during normal transfer and a wait state is inserted in the ACK (acknowledge) timing.

Caution The values in the above table are applied even when bit 2 (PIOR2) in the peripheral I/O redirection register (PIOR) is 1. At this time, the pin characteristics (I_{OH1}, I_{OL1}, V_{OH1}, V_{OL1}) must satisfy the values in the redirect destination.

Remark The maximum value of C_b (communication line capacitance) and the value of R_b (communication line pull-up resistor) at that time in each mode are as follows.

Standard mode: C_b = 400 pF, R_b = 2.7 kΩ

(2) I²C fast mode**(T_A = -40 to +85°C, 1.6 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V)**

Parameter	Symbol	Conditions		HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCLA0 clock frequency	f _{SCL}	Fast mode: f _{CLK} ≥ 3.5 MHz	2.7 V ≤ EV _{DD0} ≤ 5.5 V	0	400	0	400	0	400	kHz
			1.8 V ≤ EV _{DD0} ≤ 5.5 V	0	400	0	400	0	400	kHz
Setup time of restart condition	t _{SU:STA}	2.7 V ≤ EV _{DD0} ≤ 5.5 V		0.6		0.6		0.6		μs
		1.8 V ≤ EV _{DD0} ≤ 5.5 V		0.6		0.6		0.6		μs
Hold time ^{Note 1}	t _{HD:STA}	2.7 V ≤ EV _{DD0} ≤ 5.5 V		0.6		0.6		0.6		μs
		1.8 V ≤ EV _{DD0} ≤ 5.5 V		0.6		0.6		0.6		μs
Hold time when SCLA0 = "L"	t _{LOW}	2.7 V ≤ EV _{DD0} ≤ 5.5 V		1.3		1.3		1.3		μs
		1.8 V ≤ EV _{DD0} ≤ 5.5 V		1.3		1.3		1.3		μs
Hold time when SCLA0 = "H"	t _{HIGH}	2.7 V ≤ EV _{DD0} ≤ 5.5 V		0.6		0.6		0.6		μs
		1.8 V ≤ EV _{DD0} ≤ 5.5 V		0.6		0.6		0.6		μs
Data setup time (reception)	t _{SU:DAT}	2.7 V ≤ EV _{DD0} ≤ 5.5 V		100		100		100		μs
		1.8 V ≤ EV _{DD0} ≤ 5.5 V		100		100		100		μs
Data hold time (transmission) ^{Note 2}	t _{HD:DAT}	2.7 V ≤ EV _{DD0} ≤ 5.5 V		0	0.9	0	0.9	0	0.9	μs
		1.8 V ≤ EV _{DD0} ≤ 5.5 V		0	0.9	0	0.9	0	0.9	μs
Setup time of stop condition	t _{SU:STO}	2.7 V ≤ EV _{DD0} ≤ 5.5 V		0.6		0.6		0.6		μs
		1.8 V ≤ EV _{DD0} ≤ 5.5 V		0.6		0.6		0.6		μs
Bus-free time	t _{BUF}	2.7 V ≤ EV _{DD0} ≤ 5.5 V		1.3		1.3		1.3		μs
		1.8 V ≤ EV _{DD0} ≤ 5.5 V		1.3		1.3		1.3		μs

Notes 1. The first clock pulse is generated after this period when the start/restart condition is detected.2. The maximum value (MAX.) of t_{HD:DAT} is during normal transfer and a wait state is inserted in the ACK (acknowledge) timing.**Caution** The values in the above table are applied even when bit 2 (PIOR2) in the peripheral I/O redirection register (PIOR) is 1. At this time, the pin characteristics (I_{OH1}, I_{OL1}, V_{OH1}, V_{OL1}) must satisfy the values in the redirect destination.**Remark** The maximum value of C_b (communication line capacitance) and the value of R_b (communication line pull-up resistor) at that time in each mode are as follows.Fast mode: C_b = 320 pF, R_b = 1.1 kΩ

(4) When reference voltage (+) = Internal reference voltage (ADREFP1 = 1, ADREFP0 = 0), reference voltage (-) = AV_{REFM}/ANI1 (ADREFM = 1), target pin : ANI0, ANI2 to ANI14, ANI16 to ANI26

(T_A = -40 to +85°C, 2.4 V ≤ V_{DD} ≤ 5.5 V, 1.6 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD}, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V, Reference voltage (+) = V_{BGR}^{Note 3}, Reference voltage (-) = AV_{REFM} = 0 V^{Note 4}, HS (high-speed main) mode)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES			8			bit
Conversion time	t _{CONV}	8-bit resolution	2.4 V ≤ V _{DD} ≤ 5.5 V	17		39	μs
Zero-scale error ^{Notes 1, 2}	E _{ZS}	8-bit resolution	2.4 V ≤ V _{DD} ≤ 5.5 V			±0.60	%FSR
Integral linearity error ^{Note 1}	ILE	8-bit resolution	2.4 V ≤ V _{DD} ≤ 5.5 V			±2.0	LSB
Differential linearity error ^{Note 1}	DLE	8-bit resolution	2.4 V ≤ V _{DD} ≤ 5.5 V			±1.0	LSB
Analog input voltage	V _{AIN}			0		V _{BGR} ^{Note 3}	V

Notes 1. Excludes quantization error (±1/2 LSB).

2. This value is indicated as a ratio (%FSR) to the full-scale value.

3. Refer to **2.6.2 Temperature sensor/internal reference voltage characteristics**.

4. When reference voltage (-) = V_{SS}, the MAX. values are as follows.

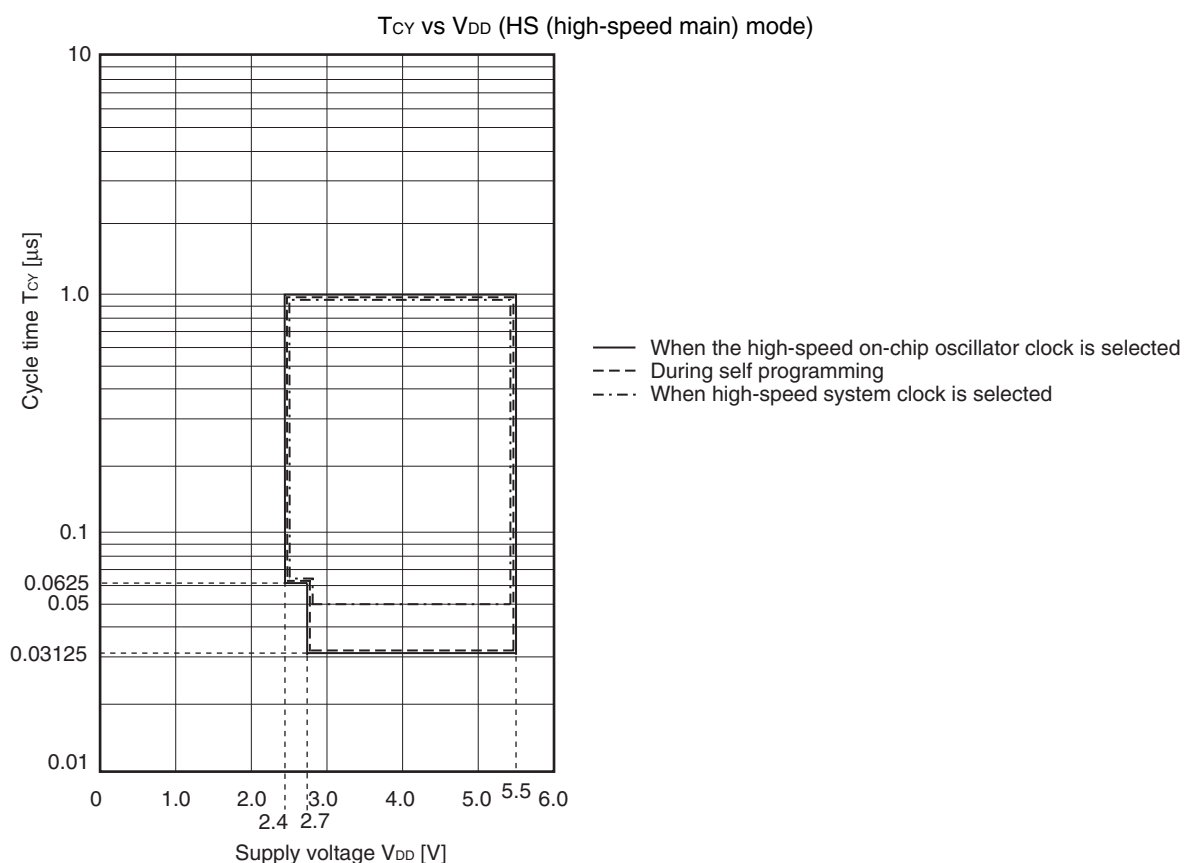
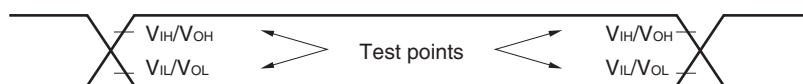
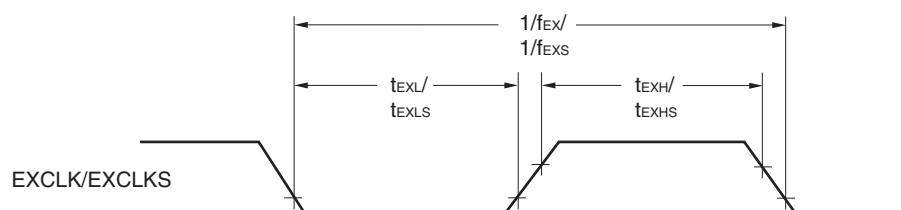
Zero-scale error: Add ±0.35%FSR to the MAX. value when reference voltage (-) = AV_{REFM}.

Integral linearity error: Add ±0.5 LSB to the MAX. value when reference voltage (-) = AV_{REFM}.

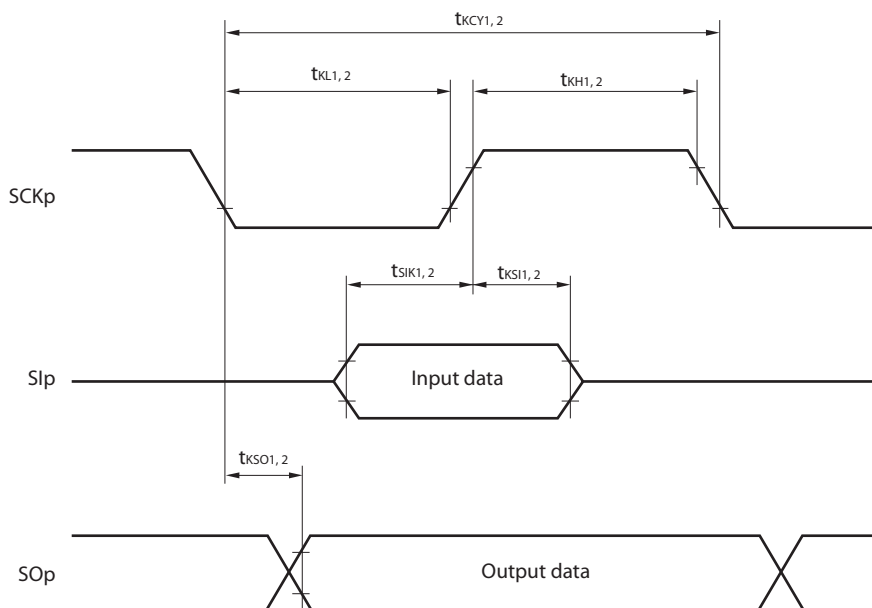
Differential linearity error: Add ±0.2 LSB to the MAX. value when reference voltage (-) = AV_{REFM}.

- Notes**
1. Total current flowing into V_{DD} and EV_{DD0} , including the input leakage current flowing when the level of the input pin is fixed to V_{DD} , EV_{DD0} or V_{SS} , EV_{SS0} . The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
 2. During HALT instruction execution by flash memory.
 3. When high-speed on-chip oscillator and subsystem clock are stopped.
 4. When high-speed system clock and subsystem clock are stopped.
 5. When high-speed on-chip oscillator and high-speed system clock are stopped. When $RTCLPC = 1$ and setting ultra-low current consumption ($AMPHS1 = 1$). The current flowing into the RTC is included. However, not including the current flowing into the 12-bit interval timer and watchdog timer.
 6. Not including the current flowing into the RTC, 12-bit interval timer, and watchdog timer.
 7. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.
 HS (high-speed main) mode: $2.7\text{ V} \leq V_{DD} \leq 5.5\text{ V}@1\text{ MHz to }32\text{ MHz}$
 $2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}@1\text{ MHz to }16\text{ MHz}$
 8. Regarding the value for current operate the subsystem clock in STOP mode, refer to that in HALT mode.

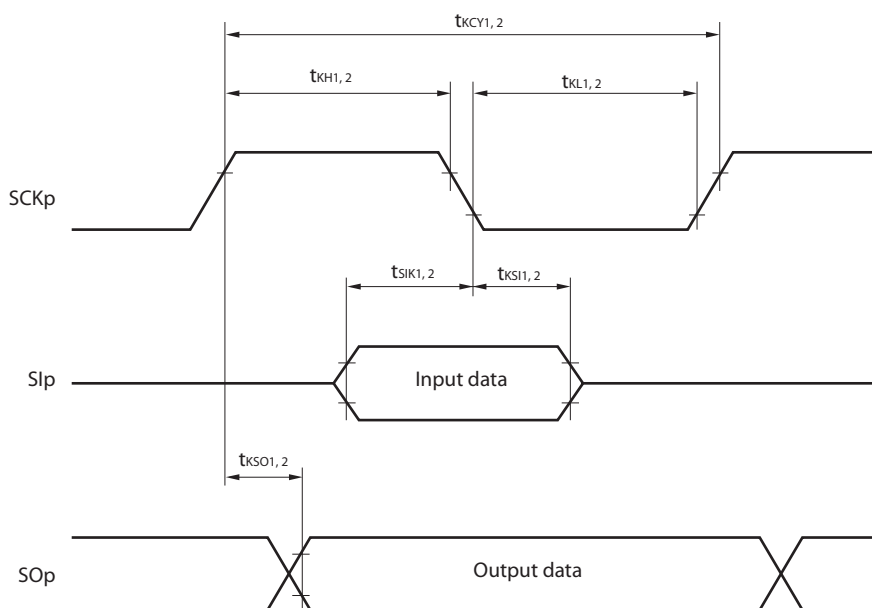
- Remarks**
1. f_{MX} : High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
 2. f_{IH} : High-speed on-chip oscillator clock frequency
 3. f_{SUB} : Subsystem clock frequency (XT1 clock oscillation frequency)
 4. Except subsystem clock operation and STOP mode, temperature condition of the TYP. value is $T_A = 25^{\circ}\text{C}$

Minimum Instruction Execution Time during Main System Clock Operation**AC Timing Test Points****External System Clock Timing**

CSI mode serial transfer timing (during communication at same potential)
(When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



CSI mode serial transfer timing (during communication at same potential)
(When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



- Remarks**
1. p: CSI number (p = 00, 01, 10, 11, 20, 21, 30, 31)
 2. m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13)

(4) During communication at same potential (simplified I²C mode)**($T_A = -40$ to $+105^\circ\text{C}$, $2.4\text{ V} \leq \text{EV}_{\text{DD}0} = \text{EV}_{\text{DD}1} \leq \text{V}_{\text{DD}} \leq 5.5\text{ V}$, $\text{V}_{\text{SS}} = \text{EV}_{\text{SS}0} = \text{EV}_{\text{SS}1} = 0\text{ V}$)**

Parameter	Symbol	Conditions	HS (high-speed main) Mode		Unit
			MIN.	MAX.	
SCLr clock frequency	f_{SCL}	$2.7\text{ V} \leq \text{EV}_{\text{DD}0} \leq 5.5\text{ V}$, $C_b = 50\text{ pF}$, $R_b = 2.7\text{ k}\Omega$		400 ^{Note1}	kHz
		$2.4\text{ V} \leq \text{EV}_{\text{DD}0} \leq 5.5\text{ V}$, $C_b = 100\text{ pF}$, $R_b = 3\text{ k}\Omega$		100 ^{Note1}	
Hold time when SCLr = "L"	t_{LOW}	$2.7\text{ V} \leq \text{EV}_{\text{DD}0} \leq 5.5\text{ V}$, $C_b = 50\text{ pF}$, $R_b = 2.7\text{ k}\Omega$	1200		ns
		$2.4\text{ V} \leq \text{EV}_{\text{DD}0} \leq 5.5\text{ V}$, $C_b = 100\text{ pF}$, $R_b = 3\text{ k}\Omega$	4600		ns
Hold time when SCLr = "H"	t_{HIGH}	$2.7\text{ V} \leq \text{EV}_{\text{DD}0} \leq 5.5\text{ V}$, $C_b = 50\text{ pF}$, $R_b = 2.7\text{ k}\Omega$	1200		ns
		$2.4\text{ V} \leq \text{EV}_{\text{DD}0} \leq 5.5\text{ V}$, $C_b = 100\text{ pF}$, $R_b = 3\text{ k}\Omega$	4600		ns
Data setup time (reception)	$t_{\text{SU:DAT}}$	$2.7\text{ V} \leq \text{EV}_{\text{DD}0} \leq 5.5\text{ V}$, $C_b = 50\text{ pF}$, $R_b = 2.7\text{ k}\Omega$	$1/f_{\text{MCK}} + 220$ ^{Note2}		ns
		$2.4\text{ V} \leq \text{EV}_{\text{DD}0} \leq 5.5\text{ V}$, $C_b = 100\text{ pF}$, $R_b = 3\text{ k}\Omega$	$1/f_{\text{MCK}} + 580$ ^{Note2}		ns
Data hold time (transmission)	$t_{\text{HD:DAT}}$	$2.7\text{ V} \leq \text{EV}_{\text{DD}0} \leq 5.5\text{ V}$, $C_b = 50\text{ pF}$, $R_b = 2.7\text{ k}\Omega$	0	770	ns
		$2.4\text{ V} \leq \text{EV}_{\text{DD}0} \leq 5.5\text{ V}$, $C_b = 100\text{ pF}$, $R_b = 3\text{ k}\Omega$	0	1420	ns

Notes 1. The value must also be equal to or less than $f_{\text{MCK}}/4$.2. Set the f_{MCK} value to keep the hold time of SCLr = "L" and SCLr = "H".

Caution Select the normal input buffer and the N-ch open drain output (V_{DD} tolerance (for the 20- to 52-pin products)/ EV_{DD} tolerance (for the 64- to 100-pin products)) mode for the SDAr pin and the normal output mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register h (POMh).

(Remarks are listed on the next page.)

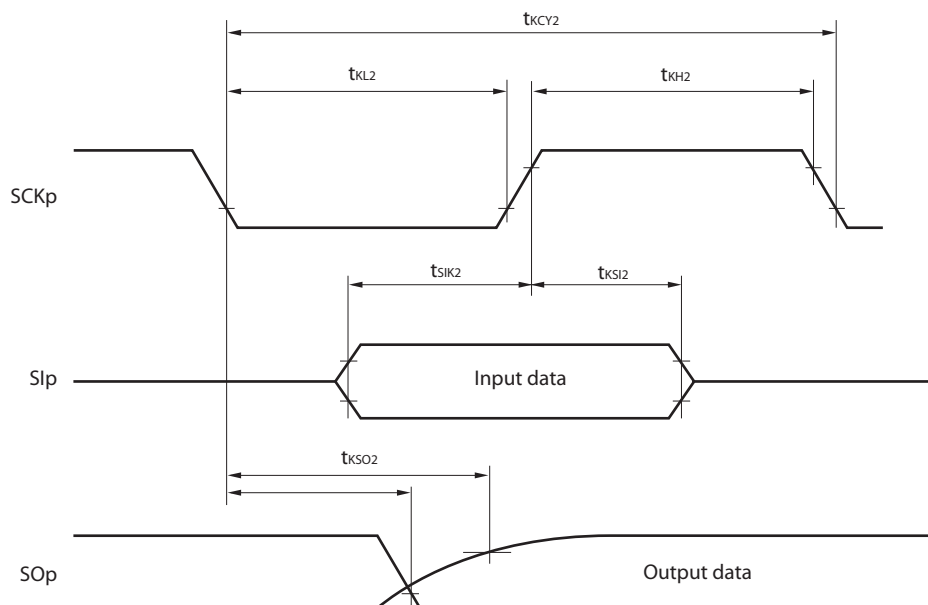
(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output) (1/3)**($T_A = -40$ to $+105^\circ\text{C}$, $2.4\text{ V} \leq \text{EV}_{\text{DD0}} = \text{EV}_{\text{DD1}} \leq \text{V}_{\text{DD}} \leq 5.5\text{ V}$, $\text{V}_{\text{SS}} = \text{EV}_{\text{SS0}} = \text{EV}_{\text{SS1}} = 0\text{ V}$)**

Parameter	Symbol	Conditions		HS (high-speed main) Mode		Unit
				MIN.	MAX.	
SCKp cycle time	t_{KCY1}	$t_{\text{KCY1}} \geq 4/f_{\text{CLK}}$	$4.0\text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5\text{ V}$, $2.7\text{ V} \leq \text{V}_b \leq 4.0\text{ V}$, $\text{C}_b = 30\text{ pF}$, $\text{R}_b = 1.4\text{ k}\Omega$	600		ns
			$2.7\text{ V} \leq \text{EV}_{\text{DD0}} < 4.0\text{ V}$, $2.3\text{ V} \leq \text{V}_b \leq 2.7\text{ V}$, $\text{C}_b = 30\text{ pF}$, $\text{R}_b = 2.7\text{ k}\Omega$	1000		ns
			$2.4\text{ V} \leq \text{EV}_{\text{DD0}} < 3.3\text{ V}$, $1.6\text{ V} \leq \text{V}_b \leq 2.0\text{ V}$, $\text{C}_b = 30\text{ pF}$, $\text{R}_b = 5.5\text{ k}\Omega$	2300		ns
SCKp high-level width	t_{KH1}		$4.0\text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5\text{ V}$, $2.7\text{ V} \leq \text{V}_b \leq 4.0\text{ V}$, $\text{C}_b = 30\text{ pF}$, $\text{R}_b = 1.4\text{ k}\Omega$	$t_{\text{KCY1}}/2 - 150$		ns
			$2.7\text{ V} \leq \text{EV}_{\text{DD0}} < 4.0\text{ V}$, $2.3\text{ V} \leq \text{V}_b \leq 2.7\text{ V}$, $\text{C}_b = 30\text{ pF}$, $\text{R}_b = 2.7\text{ k}\Omega$	$t_{\text{KCY1}}/2 - 340$		ns
			$2.4\text{ V} \leq \text{EV}_{\text{DD0}} < 3.3\text{ V}$, $1.6\text{ V} \leq \text{V}_b \leq 2.0\text{ V}$, $\text{C}_b = 30\text{ pF}$, $\text{R}_b = 5.5\text{ k}\Omega$	$t_{\text{KCY1}}/2 - 916$		ns
SCKp low-level width	t_{KL1}		$4.0\text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5\text{ V}$, $2.7\text{ V} \leq \text{V}_b \leq 4.0\text{ V}$, $\text{C}_b = 30\text{ pF}$, $\text{R}_b = 1.4\text{ k}\Omega$	$t_{\text{KCY1}}/2 - 24$		ns
			$2.7\text{ V} \leq \text{EV}_{\text{DD0}} < 4.0\text{ V}$, $2.3\text{ V} \leq \text{V}_b \leq 2.7\text{ V}$, $\text{C}_b = 30\text{ pF}$, $\text{R}_b = 2.7\text{ k}\Omega$	$t_{\text{KCY1}}/2 - 36$		ns
			$2.4\text{ V} \leq \text{EV}_{\text{DD0}} < 3.3\text{ V}$, $1.6\text{ V} \leq \text{V}_b \leq 2.0\text{ V}$, $\text{C}_b = 30\text{ pF}$, $\text{R}_b = 5.5\text{ k}\Omega$	$t_{\text{KCY1}}/2 - 100$		ns

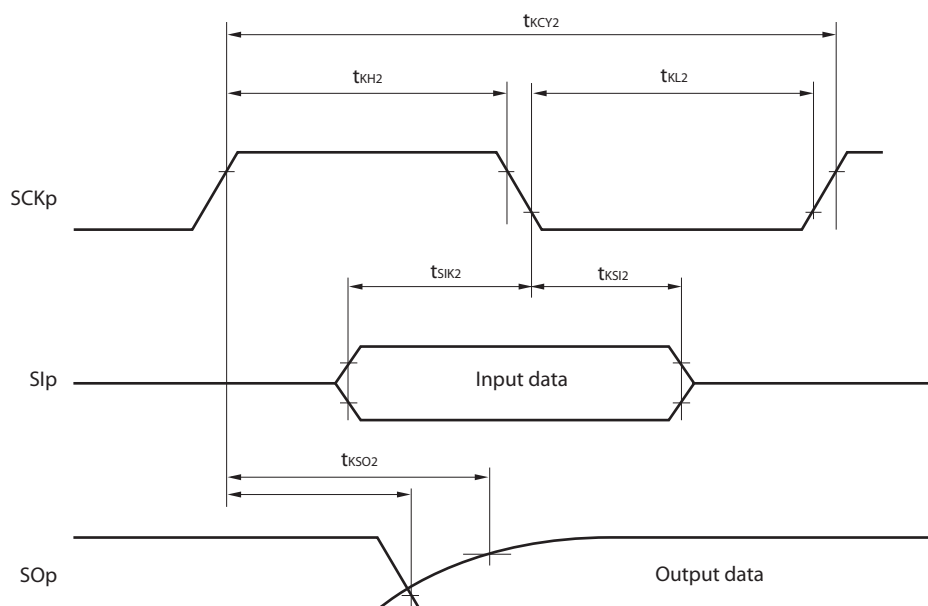
Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (V_{DD} tolerance (for the 20- to 52-pin products)/ EV_{DD} tolerance (for the 64- to 100-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL} , see the DC characteristics with TTL input buffer selected.

(Remarks are listed two pages after the next page.)

CSI mode serial transfer timing (slave mode) (during communication at different potential)
(When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



CSI mode serial transfer timing (slave mode) (during communication at different potential)
(When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)

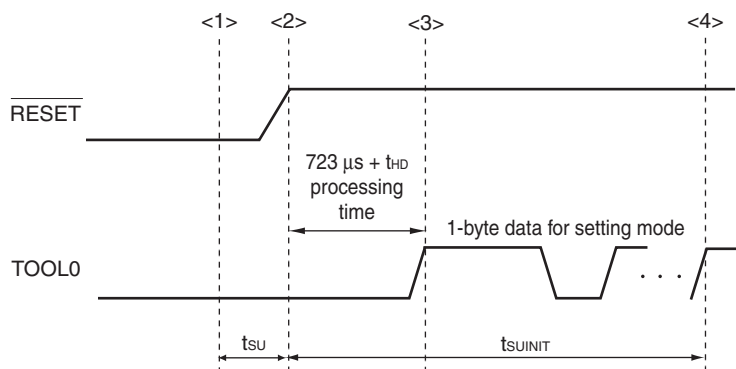


- Remarks 1.** p: CSI number (p = 00, 01, 10, 20, 30, 31), m: Unit number,
 n: Channel number (mn = 00, 01, 02, 10, 12, 13), g: PIM and POM number (g = 0, 1, 4, 5, 8, 14)
- 2.** CSI01 of 48-, 52-, 64-pin products, and CSI11 and CSI21 cannot communicate at different potential.
 Use other CSI for communication at different potential.

3.10 Timing of Entry to Flash Memory Programming Modes

(T_A = -40 to $+105^\circ\text{C}$, $2.4\text{ V} \leq \text{EV}_{\text{DD0}} = \text{EV}_{\text{DD1}} \leq \text{V}_{\text{DD}} \leq 5.5\text{ V}$, $\text{V}_{\text{SS}} = \text{EV}_{\text{SS0}} = \text{EV}_{\text{SS1}} = 0\text{ V}$)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Time to complete the communication for the initial setting after the external reset is released	t_{SUNIT}	POR and LVD reset must be released before the external reset is released.			100	ms
Time to release the external reset after the TOOL0 pin is set to the low level	t_{SU}	POR and LVD reset must be released before the external reset is released.	10			μs
Time to hold the TOOL0 pin at the low level after the external reset is released (excluding the processing time of the firmware to control the flash memory)	t_{HD}	POR and LVD reset must be released before the external reset is released.	1			ms



<1> The low level is input to the TOOL0 pin.

<2> The external reset is released (POR and LVD reset must be released before the external reset is released.).

<3> The TOOL0 pin is set to the high level.

<4> Setting of the flash memory programming mode by UART reception and complete the baud rate setting.

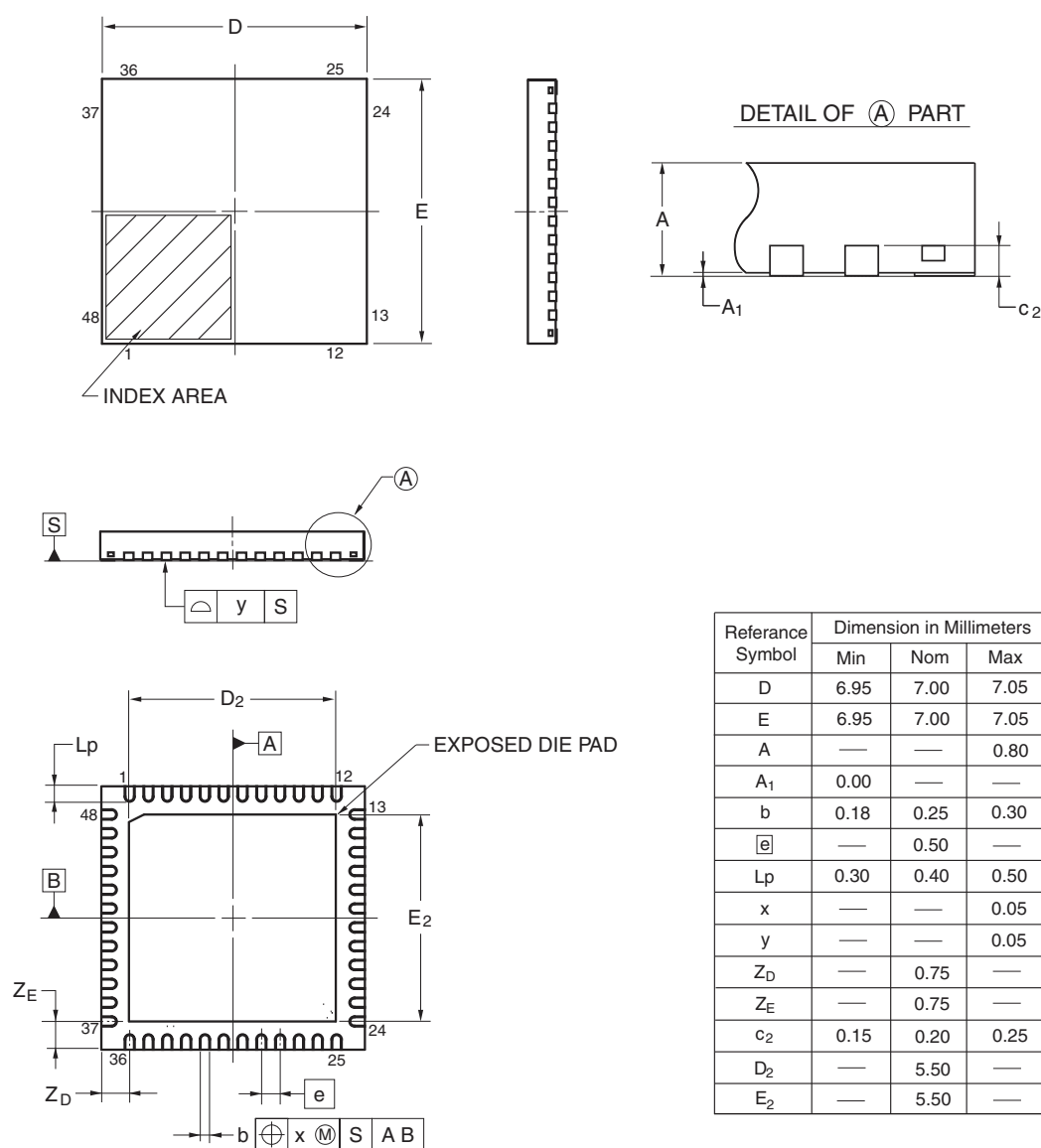
Remark t_{SUNIT} : Communication for the initial setting must be completed within 100 ms after the external reset is released during this period.

t_{SU} : Time to release the external reset after the TOOL0 pin is set to the low level

t_{HD} : Time to hold the TOOL0 pin at the low level after the external reset is released (excluding the processing time of the firmware to control the flash memory)

R5F100GAANA, R5F100GCANA, R5F100GDANA, R5F100GEANA, R5F100GFANA, R5F100GGANA,
 R5F100GHANA, R5F100GJANA, R5F100GKANA, R5F100GLANA
 R5F101GAANA, R5F101GCANA, R5F101GDANA, R5F101GEANA, R5F101GFANA, R5F101GGANA,
 R5F101GHANA, R5F101GJANA, R5F101GKANA, R5F101GLANA
 R5F100GADNA, R5F100GCDNA, R5F100GDDNA, R5F100GEDNA, R5F100GFDNA, R5F100GGDNA,
 R5F100GHDNA, R5F100GJDNA, R5F100GKDNA, R5F100GLDNA
 R5F101GADNA, R5F101GCDNA, R5F101GDDNA, R5F101GEDNA, R5F101GFDNA, R5F101GGDNA,
 R5F101GHDNA, R5F101GJDNA, R5F101GKDNA, R5F101GLDNA
 R5F100GAGNA, R5F100GCGNA, R5F100GDGNA, R5F100GEGNA, R5F100GFGNA, R5F100GGGNA,
 R5F100GHGNA, R5F100GJGNA

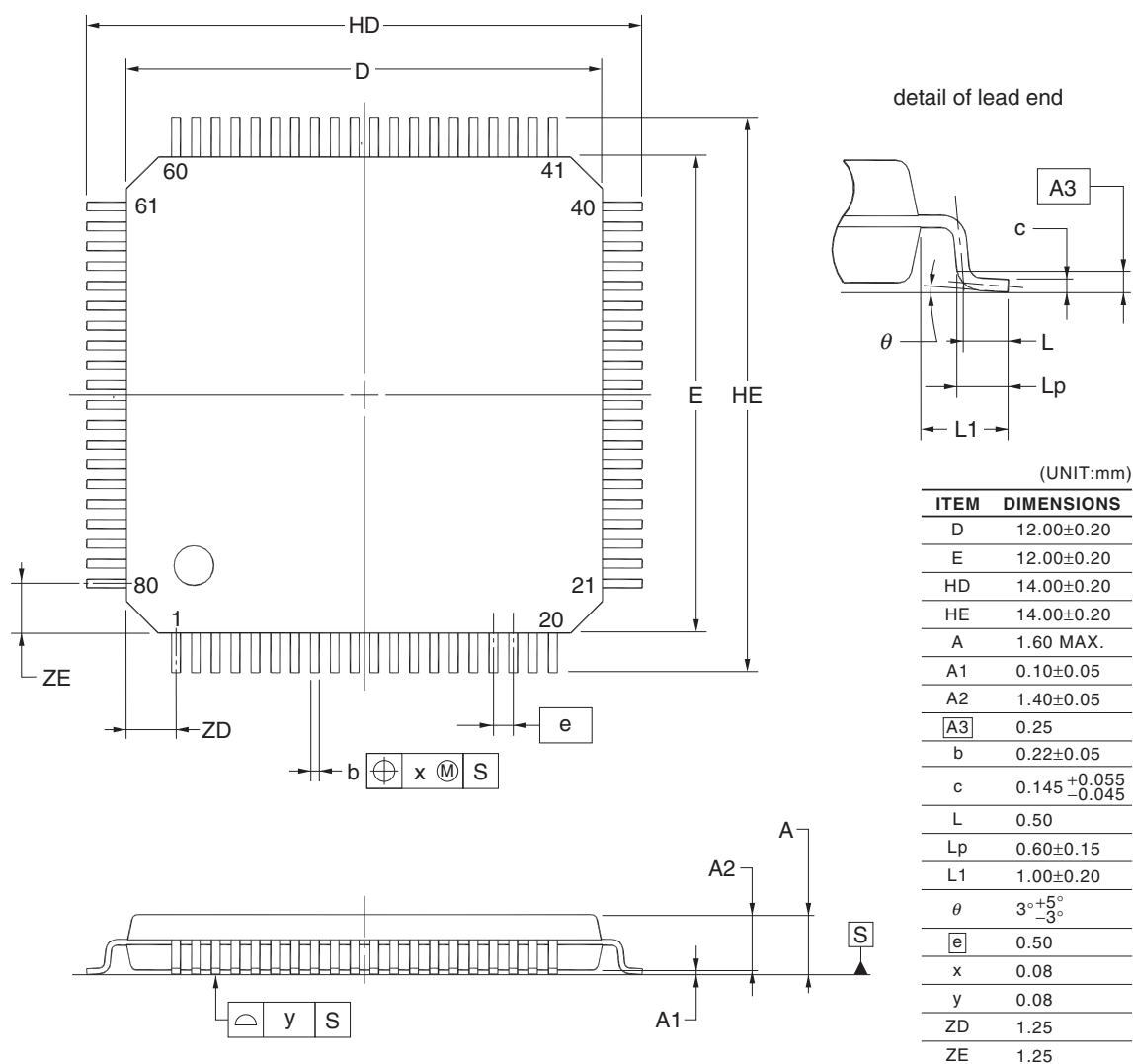
JEITA Package code	RENESAS code	Previous code	MASS(TYP.)[g]
P-HWQFN48-7x7-0.50	PWQN0048KB-A	48PJN-A P48K8-50-5B4-6	0.13



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R5F100MFAFB, R5F100MGAFB, R5F100MHAFB, R5F100MJAFB, R5F100MKAFB, R5F100MLAFB
 R5F101MFAFB, R5F101MGAFB, R5F101MHAFB, R5F101MJAFB, R5F101MKAFB, R5F101MLAFB
 R5F100MFDDB, R5F100MGDFB, R5F100MHDFB, R5F100MJDFB, R5F100MKDFB, R5F100MLDFB
 R5F101MFDDB, R5F101MGDFB, R5F101MHDFB, R5F101MJDFB, R5F101MKDFB, R5F101MLDFB
 R5F100MFGFB, R5F100MGGB, R5F100MHGFB, R5F100MJGFB

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LFQFP80-12x12-0.50	PLQP0080KE-A	P80GK-50-8EU-2	0.53

**NOTE**

Each lead centerline is located within 0.08 mm of its true position at maximum material condition.

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